

Supplementary Information

Resolving Atomistic Structure and Oxygen Evolution Activity in Nickel Antimonates

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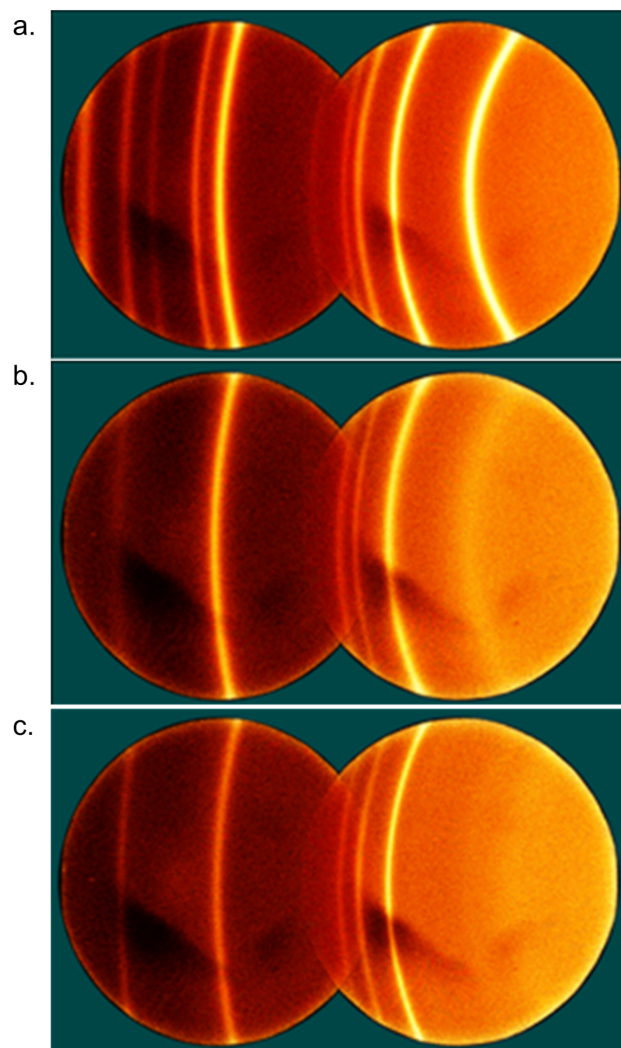


Figure S1. The raw XRD images of $\text{Ni}_x\text{Sb}_{1-x}\text{O}_z$ samples (on SiO_2/Si substrate, annealed at 700 °C in air) with a) $x = 0.33$, b) 0.50, and c) 0.63 from Figure 1a and 1b. The diffraction rings with uniform intensity indicate an equi-axed, powder-like crystallite distribution within the thin film samples.

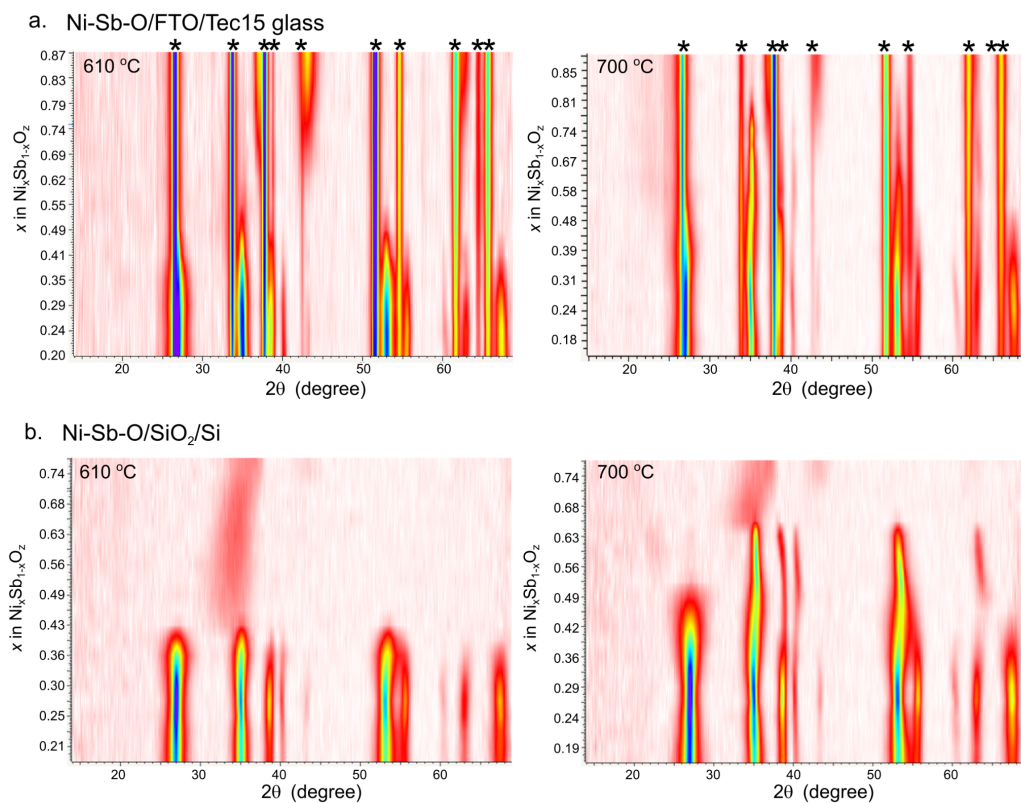


Figure S2. Heatmaps of XRD patterns for $\text{Ni}_x\text{Sb}_{1-x}\text{O}_z$ composition libraries deposited on a) FTO glass and b) SiO_2/Si substrates for both 610 and 700 °C post-deposition annealing temperature. Each heatmap is composed of a series of XRD patterns along the composition gradient and each data row corresponds to a 1D XRD pattern at that composition. The FTO substrate contributes to the peaks that are observed at all compositions and was indicated by * symbols.

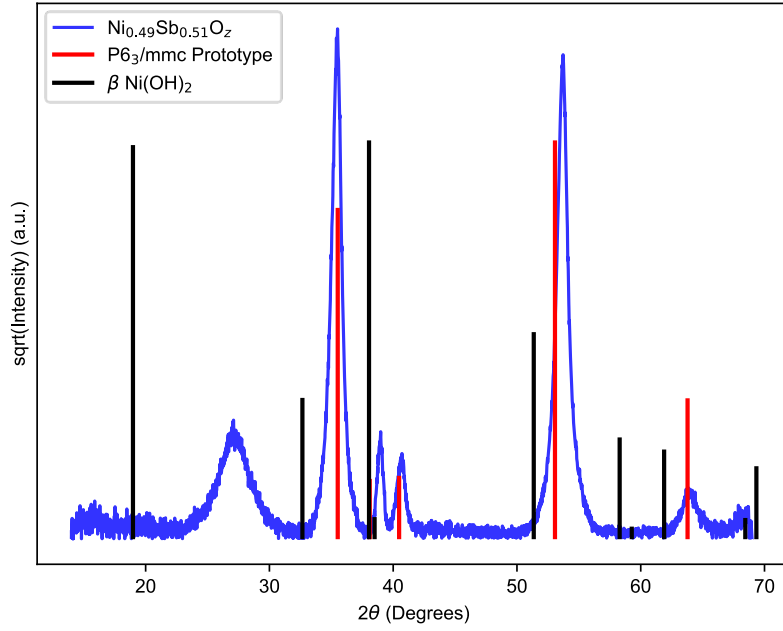


Figure S3: 1D XRD plot of the $x = 0.49$ composition. Black stick lines show calculated XRD pattern of $\beta\text{-Ni(OH)}_2$ without fitting lattice parameters. Red stick line is calculated XRD peaks of the $\text{P6}_3/\text{mmc}$ prototype with lattice constants fitted to the experimental data. The $\text{P6}_3/\text{mmc}$ prototype has the same oxygen sublattice as $\beta\text{-Ni(OH)}_2$, and additional metal cation sites. The $\beta\text{-Ni(OH)}_2$ (001) peak occurs at 19° , and is not observed in the $\text{P6}_3/\text{mmc}$ prototype.

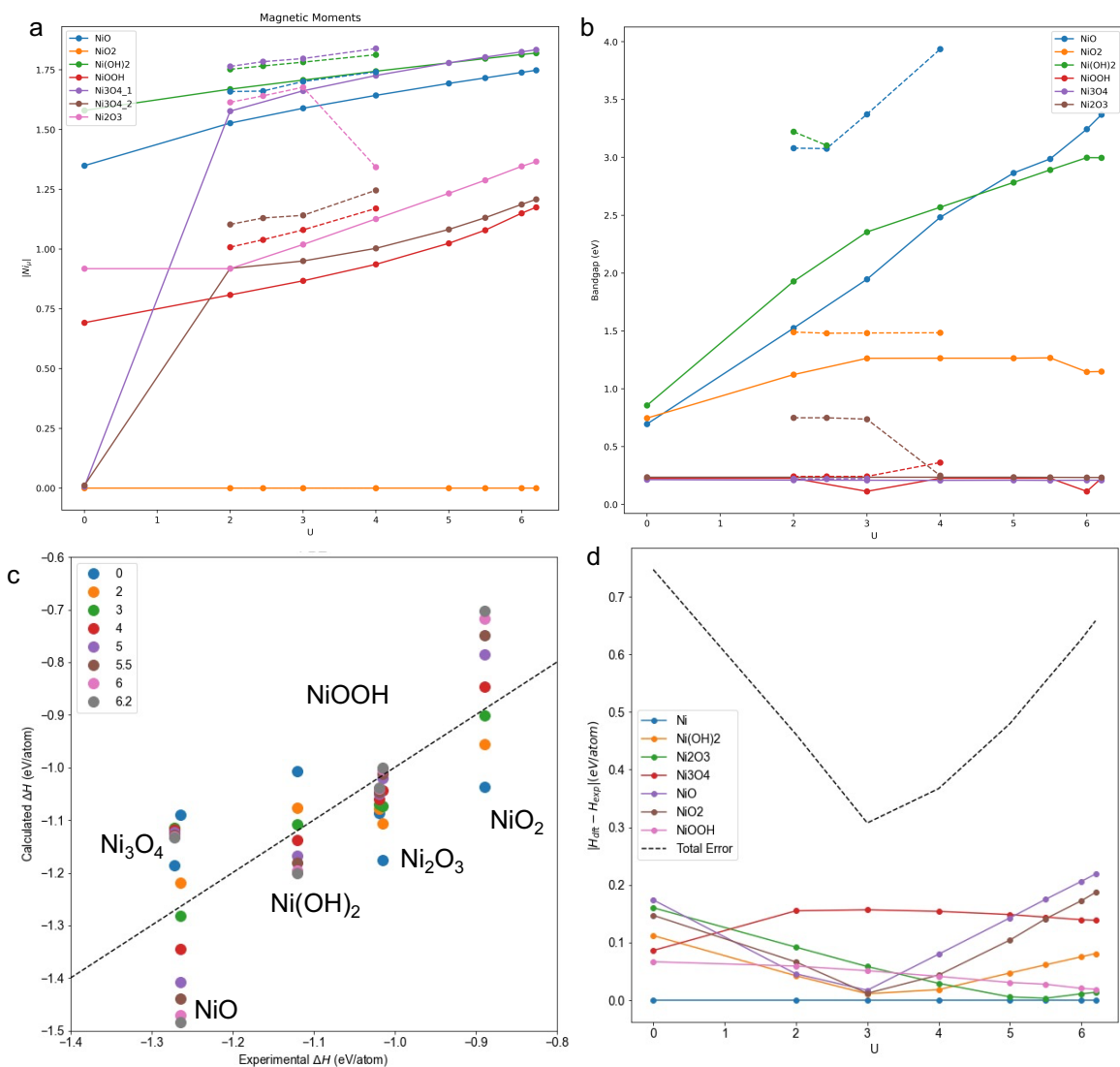


Figure S4: (a) Magnetic moments and (b) bandgap as a function of U value with both SCAN (dashed lines) and PBE functional (solid lines). (c) Enthalpy of formation parity plot against experimental values for NiO_xH_y as a with various U parameters with PBE functional. (d) Error associated with different U parameters for PBE functional

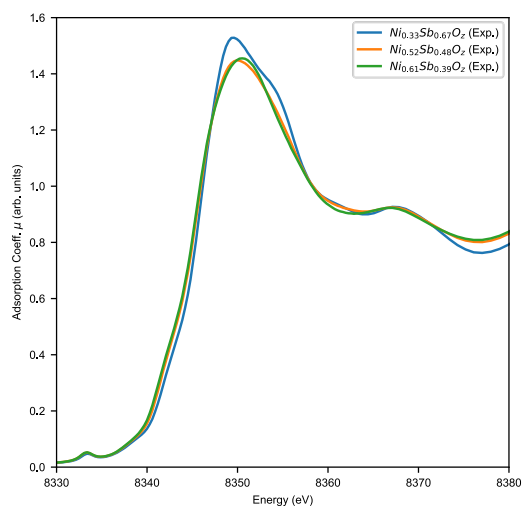


Figure S5: Experimental XAS Ni K-edge for all three samples showing nearly identical peak position.

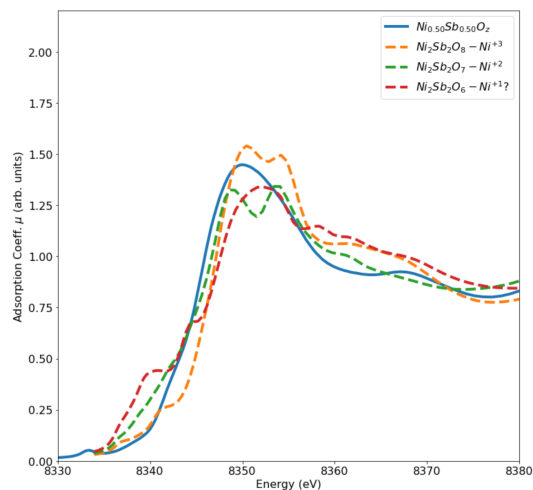


Figure S6: Experimental XAS Ni K-edge for $x=0.5$ (solid blue line), compared to $R\text{-Ni}_4\text{Sb}_4\text{O}_8$ with 0, 1, and 2 oxygen vacancies in the unit cell

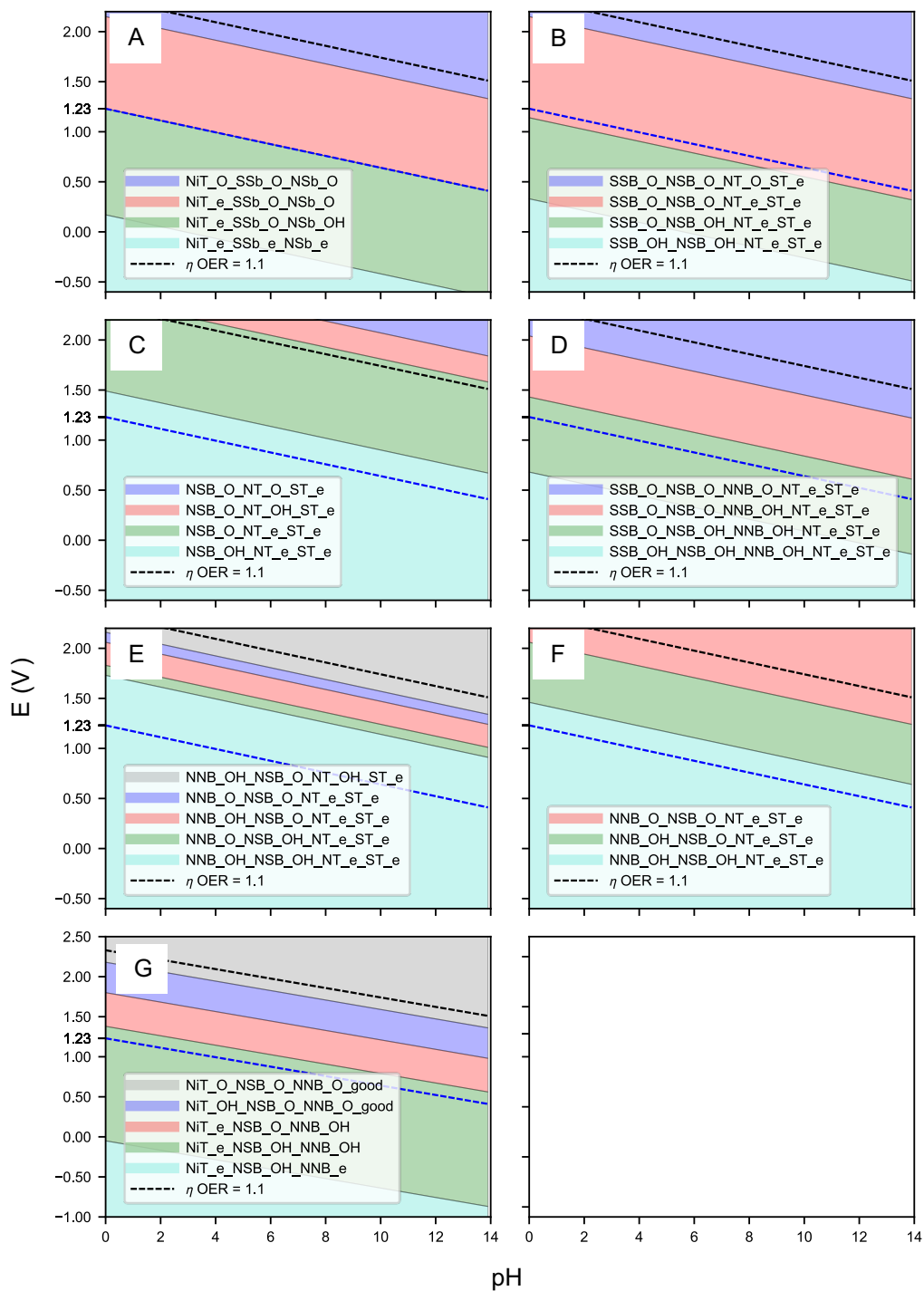


Figure S7: Surface Pourbaix Diagrams for each surface studied in this work. (a, b) R-Ni₄Sb₂O₁₂, (c, d) R-Ni₃Sb₃O₁₂, (e, f) R-Ni₄Sb₂O₁₂, and (g) hex-Ni₆Sb₃O₁₈. (a, c, e) show (110) surface terminations, (b, d, f) show (101) surfaces, and (g) is the (100) surface. The specific termination is shown in the legend of each plot where NiT/NT is O_{1c}-N, NSB is O_{2c}-NS, NNB is O_{2c}-NN,

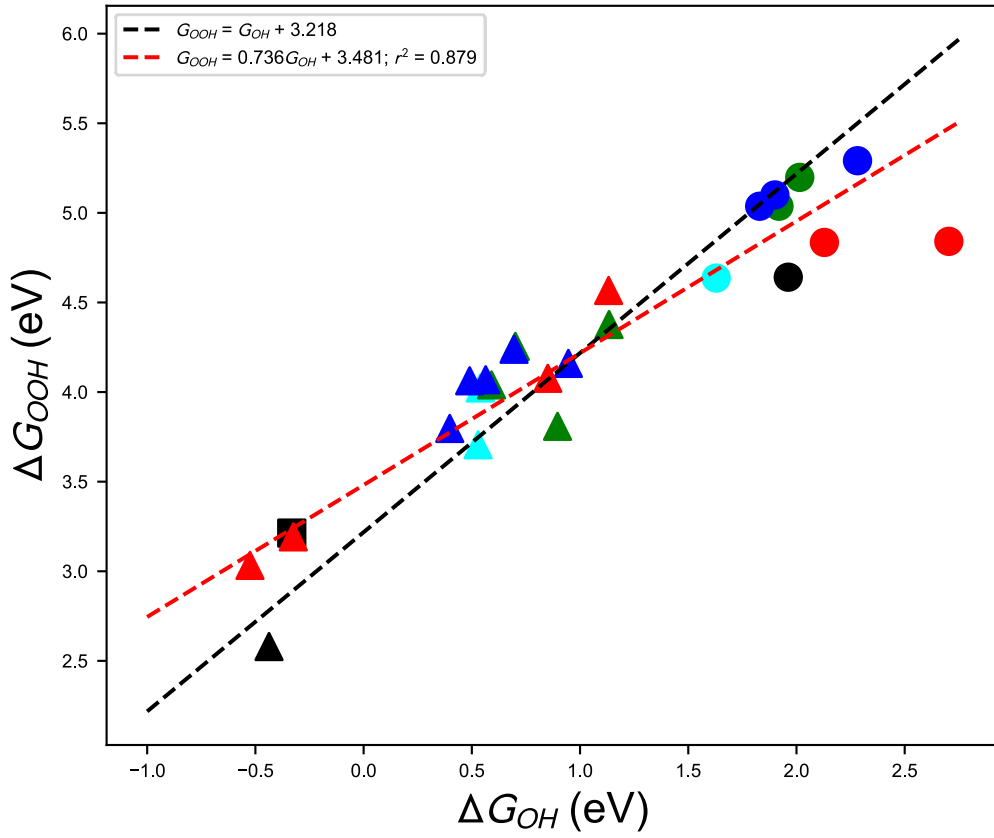


Figure S8: Scaling relationship between ΔG_{OOH} and ΔG_{OH} for the Ni-Sb-O systems. Marker symbols and colors have same meanings as in Figure 5a. Ideal scaling show as black dashed line and fitted scaling show as dashed red line.

Table S1: Summary of the bulk ordered structures and compositions used to generate Fig 2. The chemical potentials of O, Sb, and Ni are -5.793, -6.494, and -5.073 eV respectively.

Prototype	Composition	Space Group	Energy (eV/atom)	ΔE_{form} (eV/metal Atom)	ΔE_{hull} (eV/metal atom)
mp-2136	O12 Sb8	Pccn	-118.883	0.323	0.323
mp-230	O16 Sb8	Pna2_1	-144.641	0	0
mp-1705	O20 Sb8	C2/c	-166.28	0.192	0.192
mp-19009	Ni2 O2	Fm-3m	-21.733	0	0
mp-25210	Ni2 O4	C2/m	-31.618	0.85	0.85
P42/mnm	Ni2 O8 Sb2	Pmm2	-67.18	0.575	0.819
P42/mnm	Ni3 O12 Sb3	Cmm2	-103.047	0.195	0.439
P42/mnm	Ni1 O4 Sb1	Cmmm	-34.249	0.245	0.49
P42/mnm	Ni3 O12 Sb3	Cmm2	-103.048	0.195	0.439
P42/mnm	Ni3 O12 Sb3	Cmmm	-102.274	0.324	0.568

P42/mnm	Ni2 O8 Sb2	P-42_1m	-68.886	0.148	0.392
P42/mnm	Ni2 O8 Sb2	Pmma	-68.497	0.245	0.49
P42/mnm	Ni2 O8 Sb2	Pmma	-68.497	0.246	0.49
P42/mnm	Ni2 O8 Sb2	P-42_1m	-68.886	0.148	0.392
P42/mnm	Ni2 O8 Sb2	P-42_1m	-68.695	0.196	0.44
P42/mnm	Ni2 O8 Sb2	P-42_1m	-68.694	0.196	0.441
P63/mmc	Ni2 O8 Sb2	C2/m	-67.411	0.517	0.761
P63/mmc	Ni2 O8 Sb2	C2/c	-65.583	0.974	1.218
P63/mmc	Ni2 O8 Sb2	C2/m	-66.451	0.757	1.001
P63/mmc	Ni1 O4 Sb1	P2/m	-33.776	0.482	0.726
P63/mmc	Ni2 O8 Sb2	P2_1/c	-68.149	0.332	0.577
P42/mnm	Ni2 O8 Sb2	P2	-66.957	0.631	0.875
P42/mnm	Ni2 O8 Sb2	P2_12_12	-66.455	0.756	1
P42/mnm	Ni2 O8 Sb2	P2_12_12	-68.59	0.222	0.467
P42/mnm	Ni1 O4 Sb1	P2/m	-34.265	0.237	0.481
mp-1216649	Ni1 O4 Sb1	Cmmm	-29.738	2.501	2.745
mvc-5693	Ni1 O6 Sb1	Cm	-38.115	4.105	4.35
mp-23018	Ni2 O8 Sb2	C2/c	-66.906	0.643	0.888
mp-1224786	Ni1 O4 Sb1	Cmmm	-29.731	2.504	2.749
mp-674490	Ni2 O8 Sb2	P2/m	-68.169	0.327	0.572
mp-758123	Ni2 O8 Sb2	C2/m	-67.507	0.493	0.737
mvc-5033	Ni2 O12 Sb2	P2_1/c	-80.259	3.098	3.342
mp-1178209	Ni2 O8 Sb2	C222_1	-68.028	0.363	0.607
mp-761281	Ni2 O8 Sb2	Cc	-68.577	0.225	0.47
P42/mnm	Ni2 O12 Sb4	P-42_1m	-105.352	0.048	0.373
P42/mnm	Ni2 O12 Sb4	P-42_1m	-105.432	0.035	0.36
P42/mnm	Ni2 O12 Sb4	Cmmm	-106.3	-0.11	0.216
P42/mnm	Ni2 O12 Sb4	Cmmm	-106.346	-0.118	0.208
P42/mnm	Ni2 O12 Sb4	P4_2/mnm	-107.593	-0.326	0
P42/mnm	Ni2 O12 Sb4	P4_2/mnm	-107.59	-0.325	0.001
P63/mmc	Ni4 O16 Sb8	P2/c	-130.321	2.884	3.21
P63/mmc	Ni4 O16 Sb8	Pbcn	-128.537	3.033	3.359
P63/mmc	Ni4 O16 Sb8	Pbcn	-128.651	3.024	3.349
P63/mmc	Ni2 O8 Sb4	P2_1/c	-64.255	3.035	3.361
P63/mmc	Ni3 O18 Sb6	P321	-160.216	-0.195	0.13
P63/mmc	Ni3 O18 Sb6	P1	-158.213	0.027	0.353
P63/mmc	Ni3 O18 Sb6	P1	-158.234	0.025	0.351
P63/mmc	Ni3 O18 Sb6	C2	-157.2	0.14	0.466
P63/mmc	Ni3 O18 Sb6	P1	-157.682	0.086	0.412
P63/mmc	Ni1 O6 Sb2	P312	-53.015	-0.065	0.261

P63/mmc	Ni3 O18 Sb6	P321	-159.832	-0.153	0.173
P63/mmc	Ni3 O18 Sb6	C2	-157.789	0.074	0.4
mvc-8086	Ni2 O12 Sb4	C2/c	-101.426	0.702	1.028
mvc-1621	Ni2 O12 Sb4	Pmn2_1	-104.37	0.212	0.537
mp-20727	Ni1 O6 Sb2	P-31m	-53.214	-0.131	0.194
mvc-8138	Ni4 O24 Sb8	P2_1/c	-207.715	0.297	0.623
mvc-1659	Ni2 O12 Sb4	Pmn2_1	-104.381	0.21	0.535
mp-25043	Ni6 O36 Sb12	C2	-319.973	-0.17	0.156
mvc-660	Ni2 O16 Sb4	P2/c	-117.551	1.877	2.202
mp-505271	Ni4 O24 Sb8	P4_2/mnm	-215.123	-0.32	0.005
mp-1225944	Ni2 O12 Sb4	P1	-100.332	0.885	1.21
mp-19231	Ni4 O16 Sb8	P4_2/mbc	-162.617	0.193	0.519
mp-754065	Ni1 O6 Sb2	P-31m	-53.192	-0.124	0.202
mvc-8186	Ni4 O24 Sb8	P2_1/c	-207.748	0.294	0.62
mvc-8064	Ni2 O12 Sb4	C2/c	-101.425	0.702	1.028
mp-21908	Ni4 O24 Sb8	P4_2/mnm	-215.135	-0.321	0.004
mp-24845	Ni4 O24 Sb8	P4_2/mnm	-215.135	-0.321	0.004
mp-29892	Ni2 O16 Sb6	P2_1/c	-142.572	-0.097	0.148
mp-1223385	Ni2 O26 Sb10	P2_1/m	-221.404	0.358	0.521
P42/mnm	Ni4 O12 Sb2	P-42_1m	-99.087	0.618	0.781
P42/mnm	Ni4 O12 Sb2	Cmmm	-99.012	0.631	0.794
P42/mnm	Ni4 O12 Sb2	P4_2/mnm	-99.35	0.575	0.737
P42/mnm	Ni4 O12 Sb2	P4_2/mnm	-98.997	0.633	0.796
P42/mnm	Ni4 O12 Sb2	P4_2/mnm	-99.264	0.589	0.752
P42/mnm	Ni4 O12 Sb2	P4_2/mnm	-98.994	0.634	0.797
P42/mnm	Ni4 O12 Sb2	P4_2/mnm	-99.05	0.625	0.787
P42/mnm	Ni4 O12 Sb2	P4_2/mnm	-98.994	0.634	0.797
P63/mmc	Ni6 O18 Sb3	P321	-148.929	0.585	0.748
P63/mmc	Ni6 O18 Sb3	P1	-148.506	0.632	0.795
P63/mmc	Ni6 O18 Sb3	C2	-148.288	0.656	0.819
P63/mmc	Ni6 O18 Sb3	C2	-149.083	0.568	0.731
P63/mmc	Ni12 O36 Sb6	C2	-298.122	0.571	0.733
P63/mmc	Ni12 O36 Sb6	C2	-298.074	0.573	0.736
P63/mmc	Ni2 O6 Sb1	P-31m	-49.475	0.641	0.804
mvc-8086	Ni4 O12 Sb2	C2/c	-96.201	1.099	1.262
mvc-1621	Ni4 O12 Sb2	Pmn2_1	-97.206	0.932	1.095
mp-20727	Ni2 O6 Sb1	P-31m	-49.473	0.642	0.805
mvc-8138	Ni8 O24 Sb4	P-1	-190.961	1.22	1.382
mvc-1659	Ni4 O12 Sb2	Pmn2_1	-97.21	0.931	1.094
mp-25043	Ni12 O36 Sb6	C2	-298.185	0.567	0.73

mvc-660	Ni4 O16 Sb2	P2/c	-111.75	2.37	2.533
mp-505271	Ni8 O24 Sb4	P4_2/mnm	-198.681	0.576	0.739
mp-19231	Ni8 O16 Sb4	P4_2/mbc	-151.647	0.634	0.797
mp-754065	Ni2 O6 Sb1	P-31m	-49.473	0.642	0.805
mp-754065	Ni2 O6 Sb1	P-31m	-49.434	0.655	0.818
mvc-8186	Ni8 O24 Sb4	P2_1	-191.064	1.211	1.374
mvc-8064	Ni4 O12 Sb2	C2/c	-96.194	1.101	1.263
mp-21908	Ni8 O24 Sb4	P4_2/mnm	-198.693	0.575	0.738
mvc-652	Ni4 O16 Sb2	P2/c	-111.719	2.375	2.538
mp-24845	Ni8 O24 Sb4	P4_2/mnm	-198.693	0.575	0.738
mvc-4408	Ni8 O48 Sb12	C2/c	-358.878	1.885	2.178
mvc-4401	Ni8 O48 Sb12	R-3c	-358.974	1.88	2.173
mp-29892	Ni6 O16 Sb2	P2_1/c	-130.048	0.758	0.881
mvc-4408	Ni12 O48 Sb8	R-3c	-346.323	2.229	2.424
mvc-4401	Ni12 O48 Sb8	R-3c	-346.32	2.229	2.424
mvc-8023	Ni6 O24 Sb4	P-1	-173.487	2.196	2.392
mp-754951	Ni4 O12 Sb1	P1	-84.933	2.274	2.372
mp-1223385	Ni10 O26 Sb2	P2_1/m	-192.571	1.814	1.895
mp-757115	Ni10 O26 Sb2	Ama2	-192.286	1.838	1.919

Table S2: Binding energies of OER intermediates for each site on each surface. Same data is plotted in Figure 5.

Bulk Structure	Surface	Site	ΔG_{OH} (eV)	ΔG_O (eV)	$\Delta G_{OOH}-G_{OH}$ (eV)	Overpotential (V)
NiO2	200	O2c_NN	1.14	1.577	3.017	1.11
NiO2	200	O1c_N	4.176	2.214	2.679	0.984
NiO	111	O3c_N	0.9	1.232	3.545	1.083
hex-Ni2SbO6	100	O1c_N	3.938	2.309	3.007	1.079
hex-Ni2SbO6	100	O2c_NN	2.351	1.822	3.177	0.592
hex-Ni2SbO6	100	O2c_NS	2.31	1.771	3.484	0.541
r-Ni2SbO6	110	O1c_N	4.235	2.22	3.183	0.99
r-Ni2SbO6	110	O2c_NN	2.851	1.717	3.243	0.487
r-Ni2SbO6	110	O2c_NS	2.484	1.893	3.449	0.663
r-Ni2SbO6	101	O1c_N	4.434	2.515	3.118	1.285
r-Ni2SbO6	101	O2c_NN	2.946	2.05	2.913	0.82
r-Ni2SbO6	101	O2c_NS	2.429	1.728	3.554	0.596
r-NiSbO4	110	O1c_N	5.084	2.802	3.009	1.572
r-NiSbO4	110	O2c_NS	2.139	1.741	3.399	0.511
r-NiSbO4	101	O2c_NS1	2.199	1.635	3.505	0.64
r-NiSbO4	101	O2c_NS2	2.093	1.398	3.544	0.916
r-NiSbO4	101	O2c_NN	2.977	2.031	3.214	0.801

r-NiSbO ₄	101	O2c_SS	1.525	1.035	3.573	1.308
r-NiSbO ₄	101	O1c_N1	4.322	2.492	3.207	1.262
r-NiSbO ₄	101	O1c_N2	4.052	2.152	3.2	0.922
r-NiSb ₂ O ₆	110	O1c_N	4.315	1.611	2.137	1.474
r-NiSb ₂ O ₆	110	O2c_SS	0.32	0.845	3.558	1.483
r-NiSb ₂ O ₆	110	O2c_NS	1.159	1.484	3.517	0.803
r-NiSb ₂ O ₆	101	O1c_N	4.306	2.177	2.706	0.947
r-NiSb ₂ O ₆	101	O2c_NS	2.25	1.118	3.435	1.087
r-NiSb ₂ O ₆	101	O2c_SS	1.541	0.69	3.226	1.306

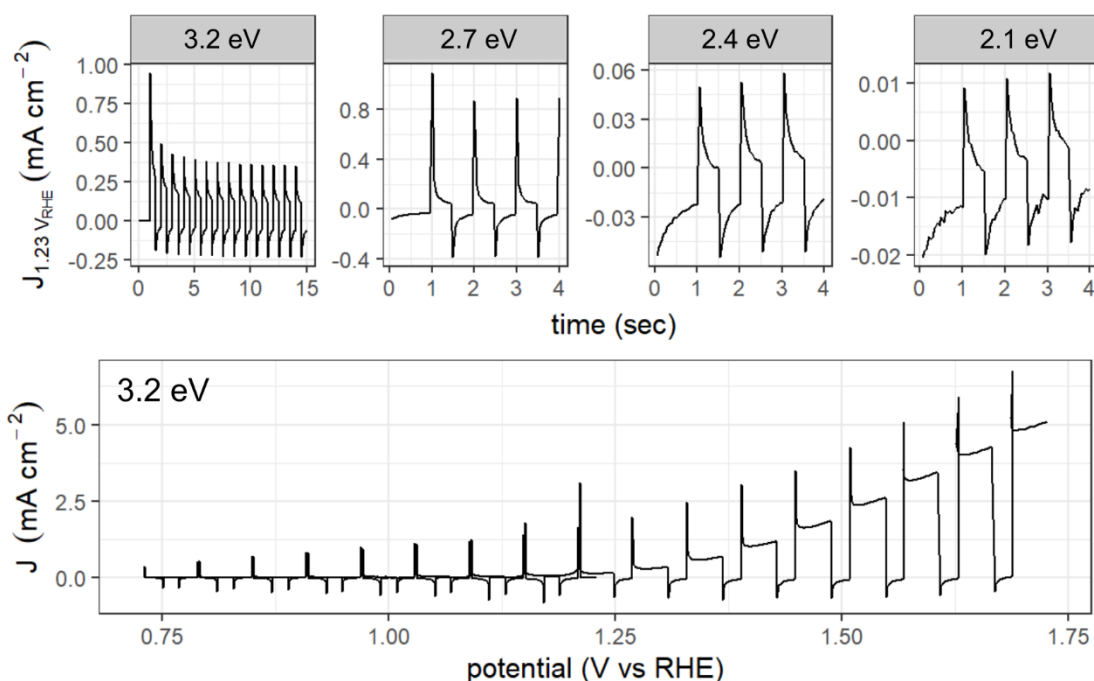


Figure S9: Photoelectrochemical (PEC) characterization of a $\text{Ni}_{0.52}\text{Sb}_{0.48}\text{O}_z$ film deposited onto $\text{SnO}_2\text{:F}$ -coated XG glass and annealed at 700 °C. All measurements are in pH 10 borate-buffered electrolyte with 0.1 M sodium sulfite as the sacrificial hole acceptor. The sequence of panels matches that of the experiments, where a series of 4 LEDs from 3.2 to 2.1 eV were used to measure toggled-illumination photoresponse under applied bias of 1.23 V vs RHE. Subsequently, the 3.2 eV LED was used in CV measurement starting at 1.23 V vs RHE with a cathodic sweep followed by an anodic sweep at a rate of 0.02 V s⁻¹. All observed photocurrents are anodic, such that every upward transient in current density corresponds to illumination turn-on and each downward transient corresponds to illumination turn-off.

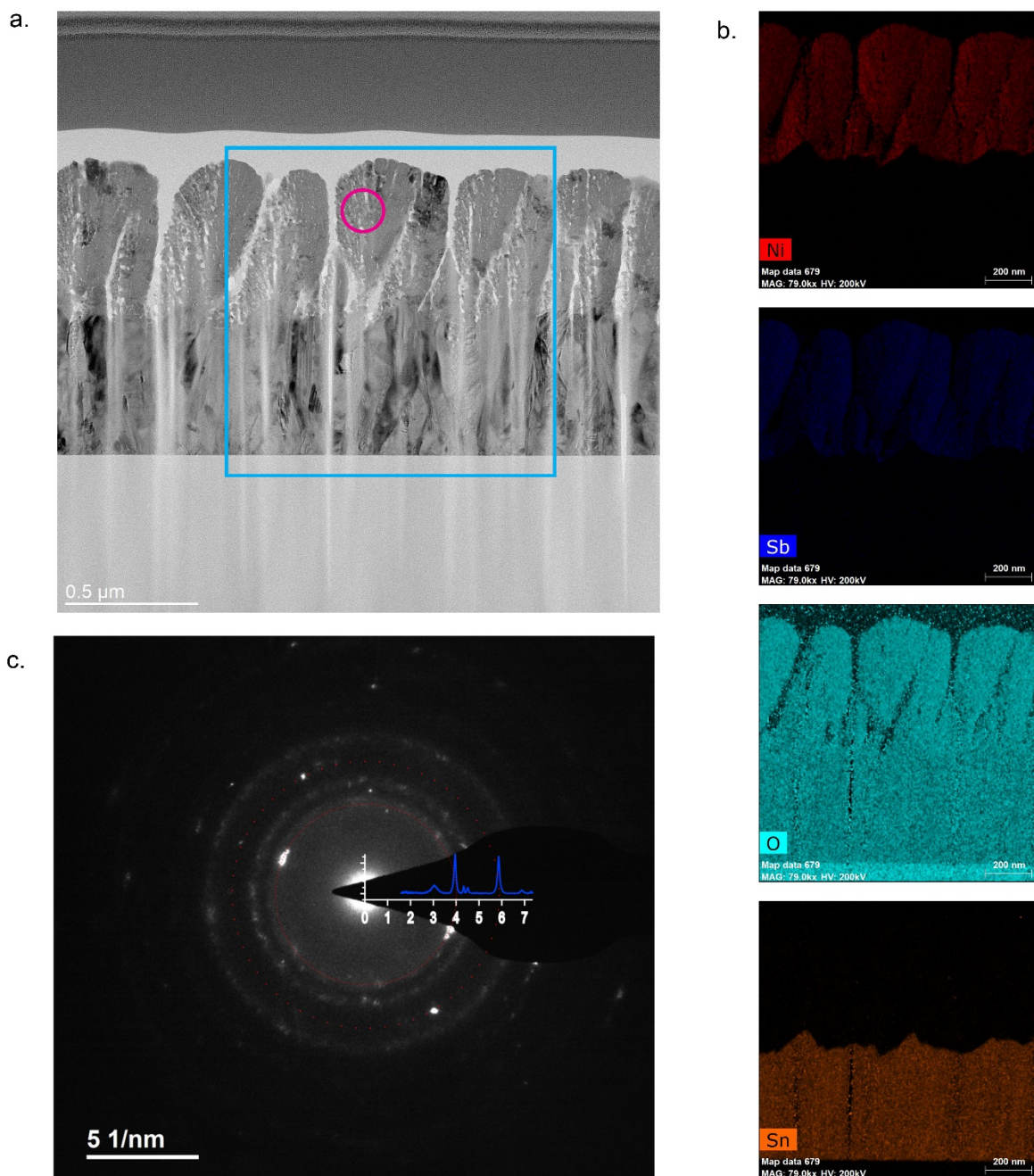


Figure S10: TEM characterization of the $\text{Ni}_{0.52}\text{Sb}_{0.48}\text{O}_z$ film (deposited on $\text{SnO}_2\text{:F}$ (FTO)-coated XG glass and annealed at 700 °C) after PEC measurements (see Figure S9) in the pH 10 electrolyte. The cross-section sample was prepared by a focused ion beam. (a) Bright field cross-section TEM image reveals an angled columnar structure that likely arises from the off-axis deposition on the rough FTO coating in the combinatorial synthesis. Hall measurements on a duplicate film indicate a high resistance, which is likely due to the lack of lateral conduction from the presence of voids in between column grains. The electrochemical results of Figure 5 indicate that electronic conduction does not interfere with characterization of catalytic activity. (b) Individual color maps for the four elements of interest: Ni, Sb, O, and Sn, obtained by energy dispersive x-ray

spectroscopy (EDX) in the region indicated by cyan square in (a). These maps confirm that there is no detectable interdiffusion of Sn from the conducting support and Ni/Sb from the deposited film. (c) The selected area electron diffraction (SAED) image taken from the area indicated by magenta circle in (a), along with the XRD pattern of the $\text{Ni}_{0.49}\text{Sb}_{0.51}\text{O}_z$ film (deposited on SiO_2/Si and annealed at 700 °C) plotted as a function of scattering vector, $1/d$, in nm^{-1} , where d is the lattice plane spacing. This XRD pattern is the same data shown in Figure 1b blue curve, where it is plotted as a function of diffraction angle, 2θ , in degrees. In addition to the absence of the strongest rutile (110) peak, the two major diffraction peaks (101) and (211) around 3.95 and 5.83 nm^{-1} , respectively, match well with the bright diffraction spots in the SAED image. The agreement of diffraction patterns confirms the two thin films grown on FTO and SiO_2/Si have the same crystalline structure, which is disordered rutile structure with space group Pnmm as theory predicted in Figure 1.